INFRA-RED Item No.: 127124

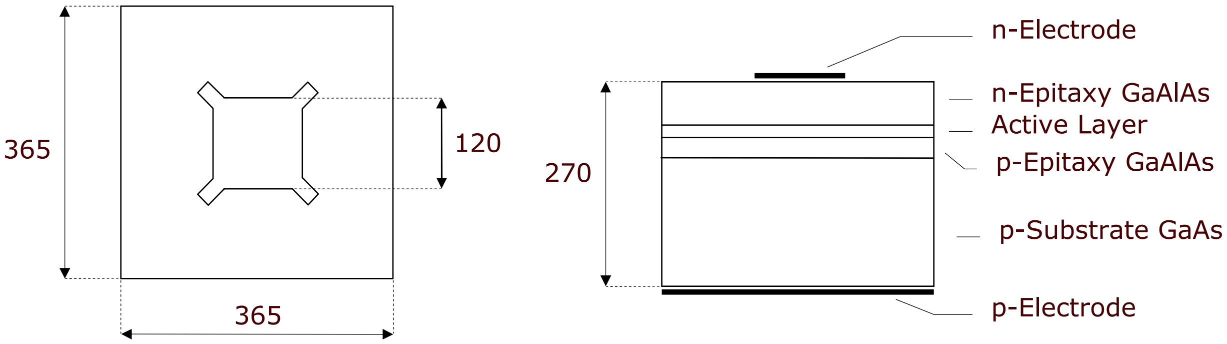
1. This specification applies to GaAlAs / GaAs Chips (substrate removed)

2. Structure

2.1 Mesa structure

2.2 Electrodes p-side (anode) Au alloy
n-side (cathode) Au alloy

3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	*Symbol*	*Conditions*	*min*	*typ*	*max*	*Unit*
Forward voltage	V_F	I_F = 20 mA		1,70	2,10	V
Reverse voltage	V_R	I_R = 5 µA			10	V
output Power *	Φ_e	I_F = 20 mA	0,6	0,8		mW
Switching time	t_r, t_f	I_F = 20 mA		40		ns
Peak wavelength	λ_P	I_F = 20 mA		740		nm

Power measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top
2) back contact on top

6. Labeling

Type	Lot No.	Φ_e typ min max	Quantity